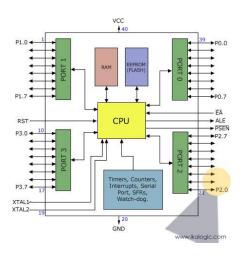
Embedded Systems Design, Spring 2025 Lecture 5



Function and architecture of microcontroller systems

Outline

- Introduction
- AVR Architecture in general
- ATMega328 Architecture in particular
- Memory Components
- Using the eeprom memory (practical example)

RISC

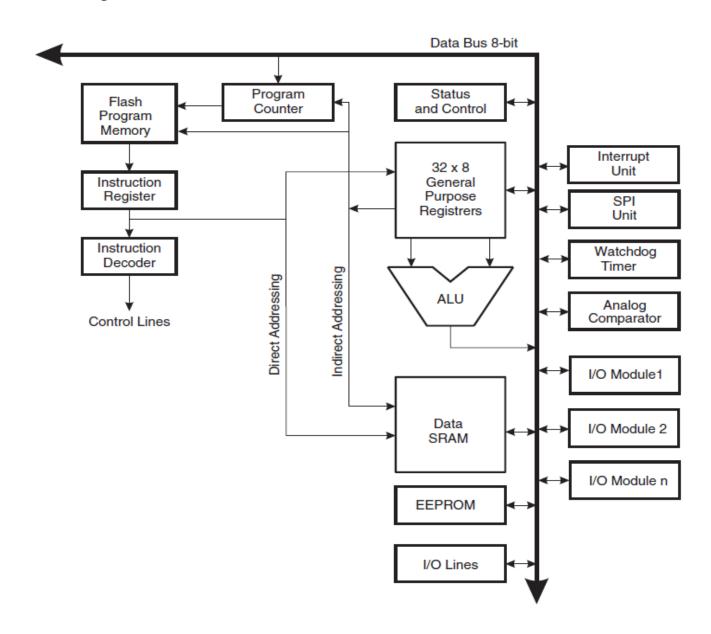
- Reduced Instruction Set Computing / (Reduced complexity)
 - Simplified instruction set (highly optimized)
 - Reduced cycles per instructions
 - For Atmel instructions are 16 bits
 - Optimized for C code execution
- Based on Harvard architecture:
 - one instruction bus where the CPU reads executable instructions;
 - one data bus to read or write the corresponding data.

RISC vs CISC

- CISC: large & complex instruction set, one instruction performs multiple low-level operations
- CISC used in processors such as Intel, AMD, gaming consoles
- RISC used in Atmel, ARM, RISC-V etc.

Assembly	Assembly
LOAD RI,A; Load value from memory address A into RI LOAD R2, B; Load value from memory address B into R2 ADD R3, RI, R2; Add RI and R2, store result in R3 STORE C, R3; Store result in memory address C	ADD C,A, B; Directly add values at memory addresses A and B, store in C

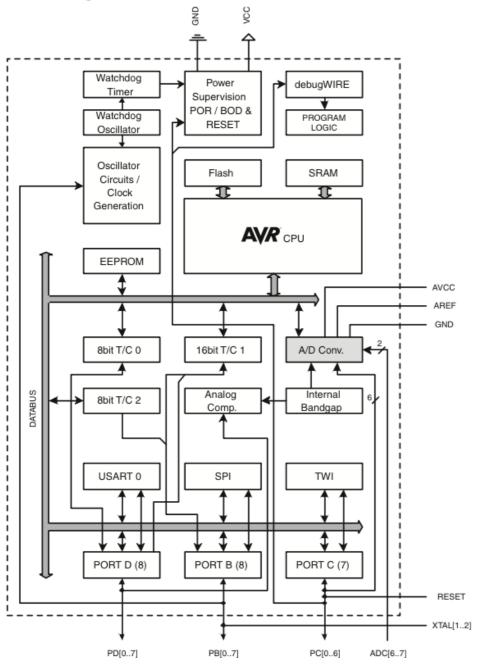
Block Diagram of the AVR Architecture



ATmega 328p

- Architecture:
 - 131 Powerful Instructions Most Single Clock Cycle Execution
 - 32 x 8 General Purpose Working Registers
 - Up to 20 MIPS Throughput at 20 MHz
- Memory:
 - Flash: 32 K Bytes
 - EEPROM: 1K Bytes
 - RAM: 2 K Bytes
 - Write/Erase Cycles: 10,000 Flash/100,000 EEPROM
- Peripherals:
 - Two 8-bit Timer/Counters
 - One 16-bit Timer/Counter
 - Six PWM Channels
 - 8 channel 10 bit ADC

Figure 2-1. Block Diagram



General Purpose Working Registers

Figure 6-2. AVR CPU General Purpose Working Registers

General Purpose Working Registers

7	0	Addr.	
R0		0x00	
R1		0x01	
R2		0x02	
R13		0x0D	
R14	,	0x0E	
R15		0x0F	
R16		0x10	
R17	,	0x11	
R26		0x1A	X-register Low Byte
R27	,	0x1B	X-register High Byte
R28		0x1C	Y-register Low Byte
R29		0x1D	Y-register High Byte
R30		0x1E	Z-register Low Byte
R31		0x1F	Z-register High Byte

Figure 6-4. The Parallel Instruction Fetches and Instruction Executions

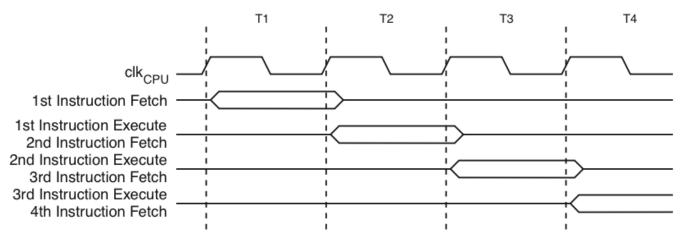
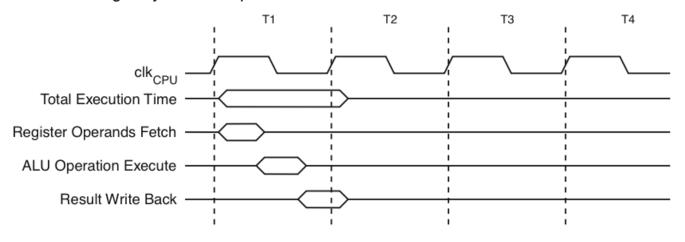


Figure 6-5. Single Cycle ALU Operation



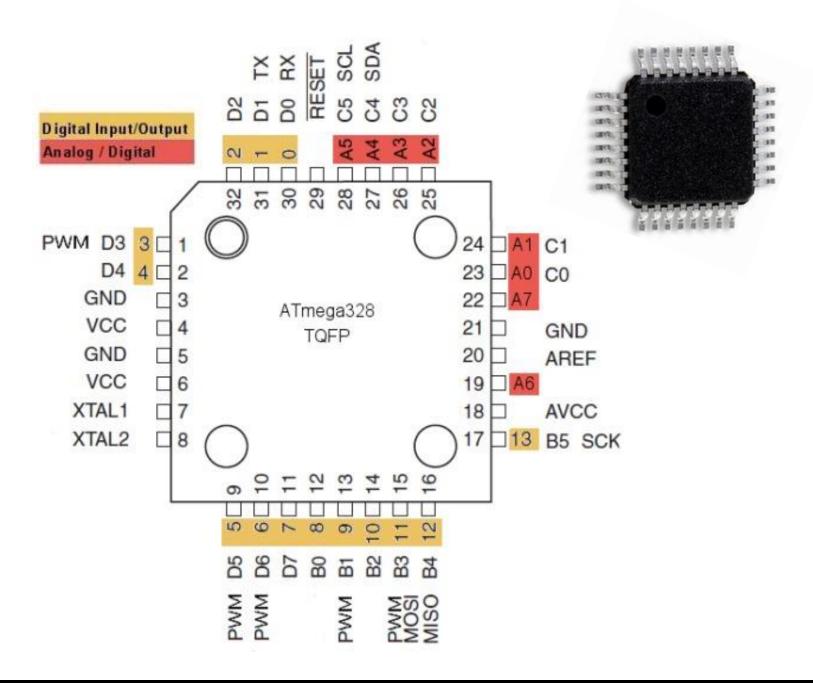
Memories

- Program Memory: 32K bytes On-chip In-System Reprogrammable Flash memory
 - 16K x 16 to hold AVR instructions (16 bit wide)
 - Divided into:
 - Bootloader section (typically your arduino bootloader)
 - Application program section
 - Non volatile
- Data memory:
 - Volatile
 - 2303 8bit locations (for registers and SRAM)

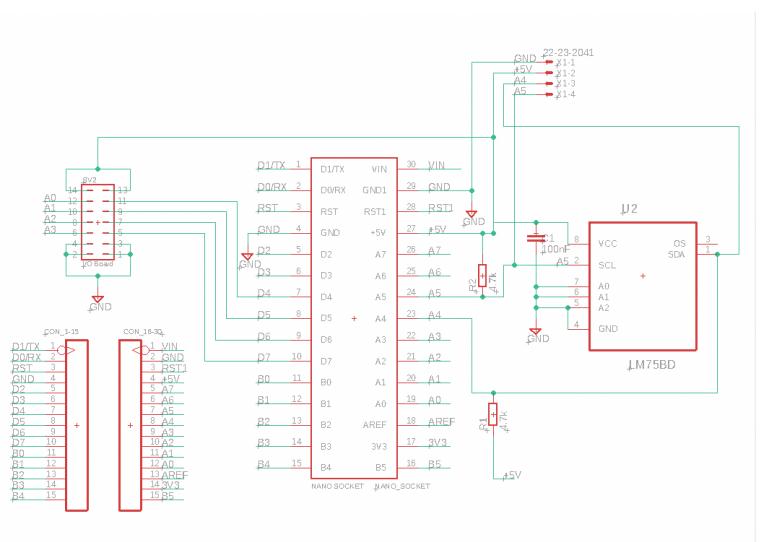
Figure 7-2. Program Memory Map ATmega88PA, ATmega168PA and ATmega328P

Program Memory 0x0000 Figure 7-3. Data Memory Map **Data Memory** Application Flash Section 0x0000 - 0x001F 32 Registers 64 I/O Registers 0x0020 - 0x005F 0x0060 - 0x00FF 160 Ext I/O Reg. 0x0100 Internal SRAM (512/1024/1024/2048 x 8) 0x04FF/0x04FF/0x0FF/0x08FF **Boot Flash Section**

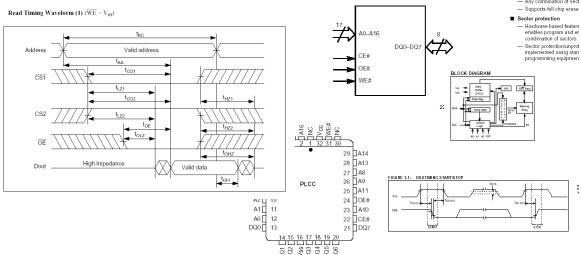
0x0FFF/0x1FFF/0x3FFF



SDU Nano Shield Schematic v 2023



Memory Components



LOGIC SYMBOL

AMD

Am29F010A

1 Megabit (128 K x 8-bit)

CMOS 5.0 Volt-only, Uniform Sector Flash Memory

Features

DISTINCTIVE CHARACTERISTICS

- Single power supply operation
- 5.0 V ± 10% for read, erase, and program operations
- Simplifies system-level
- Manufactured on 0.55 µm
- Compatible with 0.85 μr ■ High performance
- 45 ns maximum access
- Low power consumption - 20 mA typical active rea
- 30 mA typical program/∈
- <1 μA typical standby α
- Flexible sector architectu - Eight uniform sectors
- Any combination of sect
- Low Power
 30 mA Active Current
 100 µA CMOS Standby Current
 - High Reliability
 Endurance: 10⁴ or 10⁵Cycles
 Data Retention: 10 Years
 - 5V ± 10% Supply
 CMOS and TTL Compatible Inputs and Outputs

. Fast Read Access Time - 120 ns. Fast Byte Write - 200 µs or 1 ms
Self-Timed Byte Write Cycle
Internal Address and Data Latches

- Internal Control Timer - Internal Control Timer

- Automatic Clear Before Write

• Direct Microprocessor Control

- READY/BUSY Open Drain Output

- DATA Polling

- JEDEC Approved Byte-Wide Pinout Commercial and Industrial Temperature Ranges

Description

The AT28C64 is a low-power, high-performance 8,192 words by 8-bit nonvolatile Electrically Erasable and Programmable Read Only Memory with popular, easy to use features. The device is manufactured with Atmel's reliable nonvolatile technology.

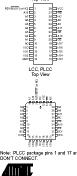
■ Embedded Algorithms

Embedded Erase algorithm automatically

Pin Configurations

Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
OE .	Output Enable
WE	Write Enable
1/00 - 1/07	Data Inputs/Outputs
RDY/BUSY	Ready/Busy Output
NC	No Connect
DC	Don't Connect
	TSOP Top View





PDIP SOIC

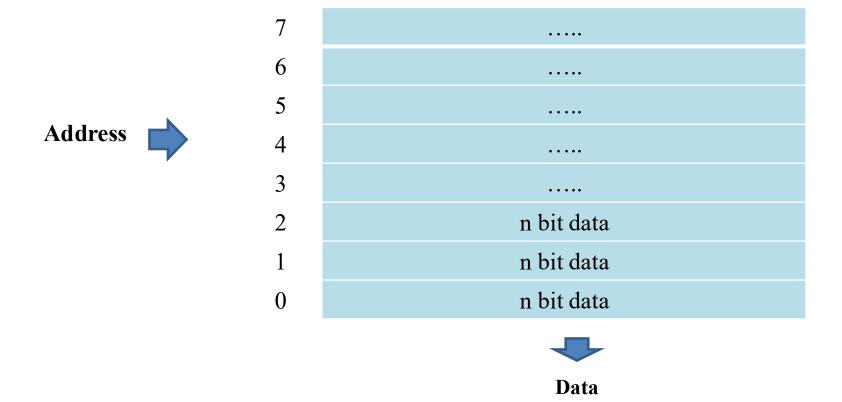


64K (8K x 8) Parallel **EEPROMs**

AT28C64 AT28C64X



General Memory Structure



ROM/RAM Memory

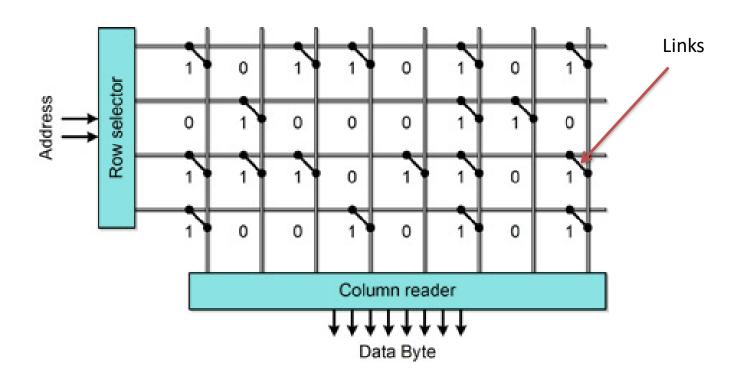
ROM – Read Only Memory

- **EPROM** Erasable Programmable Read Only Memory
- **EEPROM** Electrically Erasable Prom (E²Prom)
- FLASH

RAM – Random Access Memory

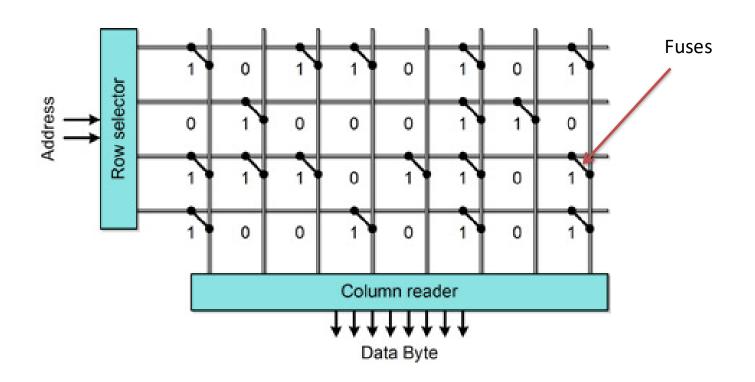
- SRAM Static RAM
- **DRAM** Dynamic RAM

ROM (Read Only Memory)



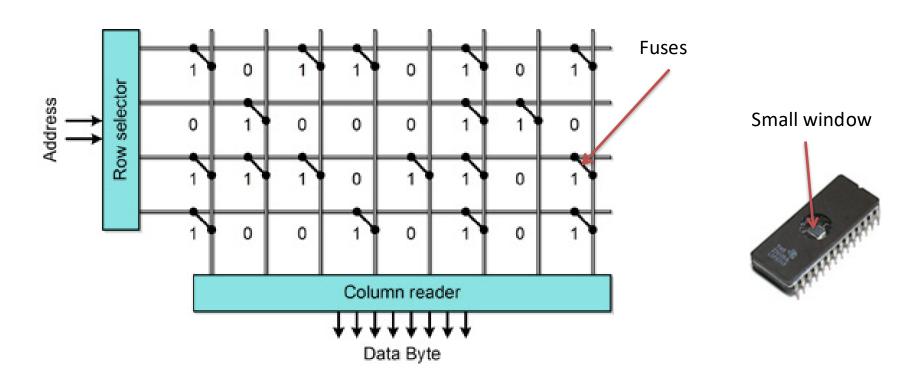
- Links are "pre-fabricated" using special masks, leading to no possibility for changing them later.
- Expensive to make

PROM (Programmable Read Only Memory)



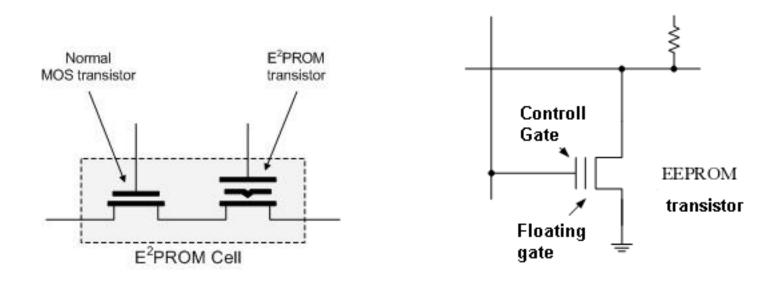
- Links are initially intact fuses. By applying a high voltage to a specific row and column a fuse can be "blown" leading to creation of a 0.
- Easy to program, low cost

EPROM (Erasable Programmable Read Only Memory)



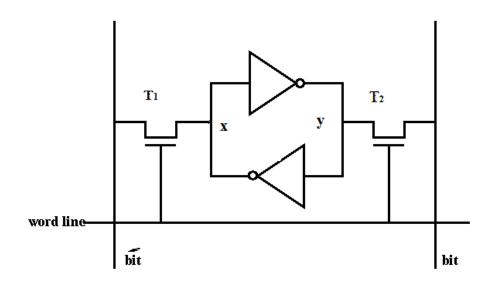
- Behavior similar to PROM with the possibility to reset the fuses to intact by use of ultra-violet light.
- Easy to program, low cost, used for many years

EEPROM (Electrically Erasable Programmable Read Only Memory)



- Behavior similar to EPROM with the possibility to reset the fuses to intact by use of field electron emission
- Each cell needs a write, a read and a reset transistor
- Easy to program in situ, without the need of removal
- Limited number of re-writes

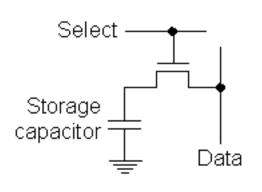
SRAM memory cell



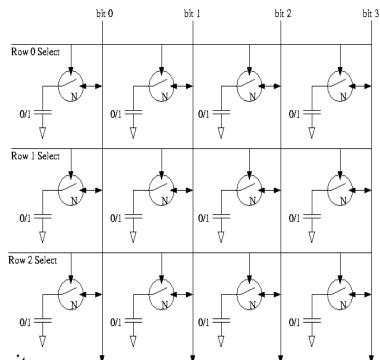
Basic six-transistor static memory cell

- Idle state: word line keeps the T1 and T2 in the OFF state
- Read state: word line puts the T1 and T2 in the ON state, bit and ~bit are read
- Write state: Bit and ~bit are changed, word line not used

DRAM memory cell

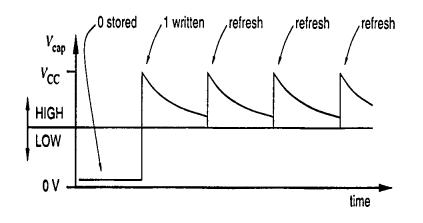


Dynamic RAM use a MOS capacitor as the basic storage cell



- The switch is used to store a charge in the capacitor
- Due to leakage of the capacitor, it needs refreshing
- Slower than SRAM

DRAM refresh



Voltage stored in a DRAM cell after writing and refresh operations

Reading/Writing to Atmega328 EEPROM

• Help from the AVR-GCC eeprom library functions #include <avr/eeprom.h>

 Many functions for writing or reading bytes, ints, floats or even byte blocks

```
void eeprom_write_byte(uint8_t *pAddress, uint8_t value)
void eeprom_write_float(float *pAddress, float value)
...
uint8_t eeprom_read_byte(const uint8_t * pAddress)
float eeprom_read_float(const float * pAddress)
```

Example – writing a byte to eeprom address 0

```
#include ... //add necessary includes for the code to work
#include <avr/eeprom.h>
void main() {
                                              What will be written
       uint8 t rb, wb = 50;
       unsigned int addr = 0; //eeprom address is 0 in this
program
                                              What will be read
       uart init();
       io redirect();
       while (1) {
               eeprom write byte ((uint8 t *)addr, wb); //write
               rb = eeprom read byte((uint8 t *)addr); //read
               printf("read from eeprom %d \n", rb); //print
               delay ms(1000);
               wb++; //write a different number next time
```

Task

- Use your arduino, shield + digital I/O board to:
 - Read the temperature every second from the sensor
 - Read a stored temperature every second from the eeprom
 - Display both the current and the saved temperatures every second
 - If the last button is pressed on your DIO board, save the current temperature on eeprom (as int, or as float)

Try restarting your arduino and see what happens!